

2.0A Surface Mount High Efficiency Rectifiers - 50V-1000V

Features

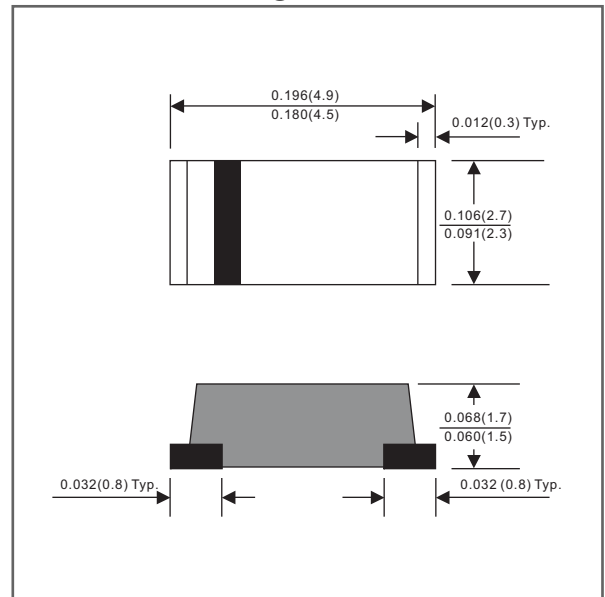
- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- High current capability.
- Ultrafast recovery time for high efficiency.
- High surge current capability.
- Glass passivated chip junction.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen free parts, ex. MURA205G-H.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, JEDEC DO-214AC / SMA
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.05 gram

Package outline

SMA



Dimensions in inches and (millimeters)

Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	Ambient temperature = 50°C	I_O			2.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}			50	A
Reverse current	$V_R = V_{RRM}$ $T_J = 25^\circ\text{C}$	I_R			5.0	μA
	$V_R = V_{RRM}$ $T_J = 100^\circ\text{C}$				150	
Thermal resistance	Junction to ambient	$R_{\theta JA}$		20		$^\circ\text{C}/\text{W}$
Diode junction capacitance	$f=1\text{MHz}$ and applied 4V DC reverse voltage	C_J		25		pF
Storage temperature		T_{STG}	-65		+175	$^\circ\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	T_{RR}^{*5} (nS)	Operating temperature T_J ($^\circ\text{C}$)
MURA205G	50	35	50	1.00	50	-55 to +150
MURA210G	100	70	100			
MURA220G	200	140	200			
MURA240G	400	280	400	1.30		
MURA260G	600	420	600	1.70	75	
MURA280G	800	560	800			
MURA2100G	1000	700	1000			

*1 Repetitive peak reverse voltage

*2 RMS voltage

*3 Continuous reverse voltage

*4 Maximum forward voltage@ $I_F=2.0\text{A}$

*5 Maximum Reverse recovery time, note 1

Note 1. Reverse recovery time test condition, $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$

Rating and characteristic curves

FIG.1-TYPICAL FORWARD

CHARACTERISTICS

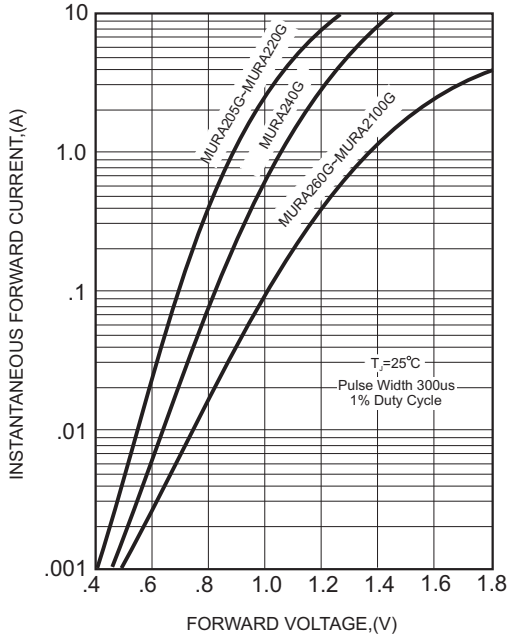


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

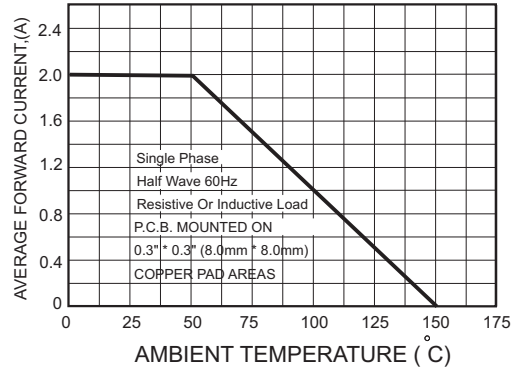
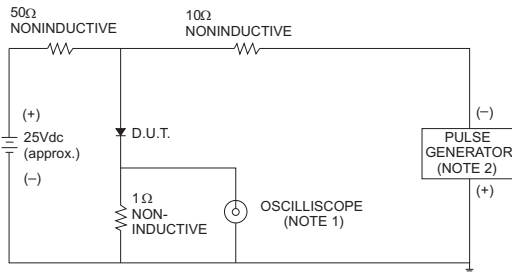


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

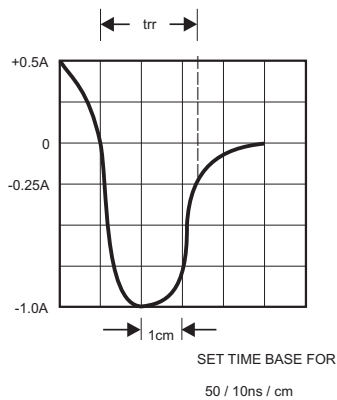


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

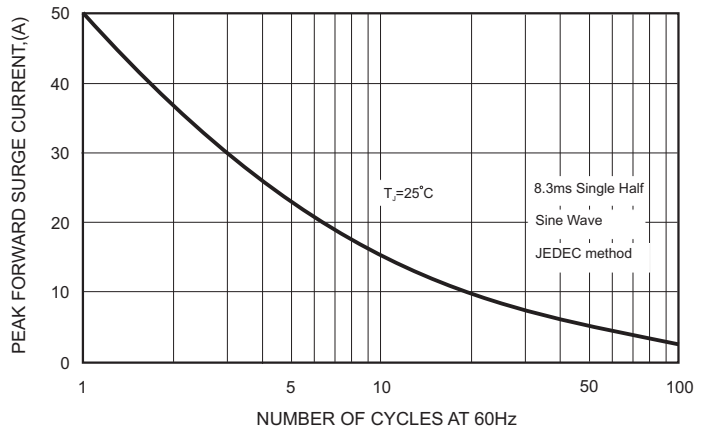


FIG.5-TYPICAL JUNCTION CAPACITANCE

